

CLAIM AMENDMENTS

1. (Currently Amended) A semiconductor device ~~on which comprising:~~
a plurality of semiconductor elements, each semiconductor element having first and second main electrodes and a control electrode ~~are arranged, comprising:~~
a semiconductor substrate having ~~one~~ a first principal plane on which the first and second main electrodes and the control electrode are ~~formed~~ located;
a film ~~which is formed~~ over the first main electrode and the control electrode ~~so as to insulate, insulating~~ the first main electrode and the control electrode from the second main electrode, and ~~is~~ made of a polymer material with a low dielectric constant; and
a chip surface electrode ~~formed~~ over the film and the second main electrode and connected to a ground potential, wherein the second main electrode is provided with the ground potential through the chip surface electrode.

2. (Currently Amended) ~~A~~ The semiconductor device according to claim 1, ~~wherein~~ including a first pad connected to the first electrode and a second pad connected to the second electrode ~~are formed and located~~ on a second principal plane ~~on the~~ opposite side of the first principal plane of the semiconductor on which the electrodes ~~of the semiconductor substrate~~ are ~~formed~~ located.

3. (Currently Amended) ~~A~~ The semiconductor device according to claim 1, wherein the semiconductor substrate is ~~made from~~ one of SiC ~~or~~ and sapphire.

4. (Currently Amended) A semiconductor device ~~on which comprising:~~
a plurality of semiconductor elements, each semiconductor element having first and second main electrodes and a control electrode ~~are formed, comprising:~~
a semiconductor substrate having ~~one~~ a first principal plane on which the first and second main electrodes and the control electrodes are ~~formed~~ located; and
a protecting film ~~formed~~ over the first and second main electrodes and the control electrodes, and made of a polymer material with a low dielectric constant.

5. (Currently Amended) A semiconductor device ~~on which comprising:~~
a plurality of semiconductor elements, each semiconductor element having first and second main electrodes and a control electrode ~~are formed, comprising:~~

a semiconductor substrate having ~~one~~ a first principal plane on which the first and second main electrodes and the control electrodes are ~~formed~~ located;

a metal layer ~~which is formed~~ on a second principal plane ~~on the~~, opposite side of the first principal plane of the semiconductor substrate and which is grounded;

a film ~~formed~~ over the first and second main electrodes and the control electrodes and made of a polymer material with a low dielectric constant; and

a surface layer ~~which is formed~~ on the film made of a polymer material with a low dielectric constant and which is ~~made of~~ the same material as ~~that of~~ the grounded metal layer.

6. (Currently Amended) ~~A~~ The semiconductor device according to claim 5, wherein the surface layer is electrically connected to the grounded metal layer.